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	48	5,904,517	05/1999	Gardner et al.		438	197		<u> </u>
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## U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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ATTY. DOCKET NO. Mi22-2426 SERIAL NO. 10/690,029

APPLICANT: Garo J. Derderian

FILING DATE October 20, 2003

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